

Object Parameter Retrieval using Inverse Electron Diffraction including Potential Differences

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Object data can be directly retrieved from the electron microscope exit wave function without using trial-and-error iterative matching [1]. The retrieval of local data, e.g. thickness, orientation, potential, as a basis of a general object reconstruction, can be gained by linearizing the scattering problem and constructing regularized and generalized inverse matrices. Starting e.g. from a hologram, where all reflections \mathbf{g} are separately reconstructed, the moduli (A) and phases (P) of the exit plane wave Φ^{exp} are determined for each \mathbf{g} (cf. Fig. 1, Fouriertransform of the hologram and selected \mathbf{g}). Theoretical waves Φ^{th} are then calculated using the dynamical scattering matrix M for an a priori model characterized by the number of beams and the scattering potential. With a suitable experimentally predetermined trial average beam orientation \mathbf{K}_{Oxy} and a sample thickness t_0 as a free parameter, a perturbation approximation yields both Φ^{th} and M as linear functions of parameters to be retrieved. The analytic form of the equations enable the inverse solution $[t, \mathbf{K}_{xy}, \dots] = M_{\text{inv}} \cdot (\Phi^{\text{exp}} - \Phi^{\text{th}})$, thus yielding directly for each image pixel (i,j) the local thickness $t(i,j)$ and the local beam orientation $\mathbf{K}_{xy}(i,j)$. Generalizing of M_{inv} avoids the ill-posedness, the problem, however, is now ill-conditioned. As pointed out in different previous analyses (cf. e.g. [2]) a regularization of the retrieval procedure requires the control of the confidence and stability region. As shown in the retrieved t and \mathbf{K}_{xy} of Fig.1, the modeling errors because of the potential difference are the remaining fault.

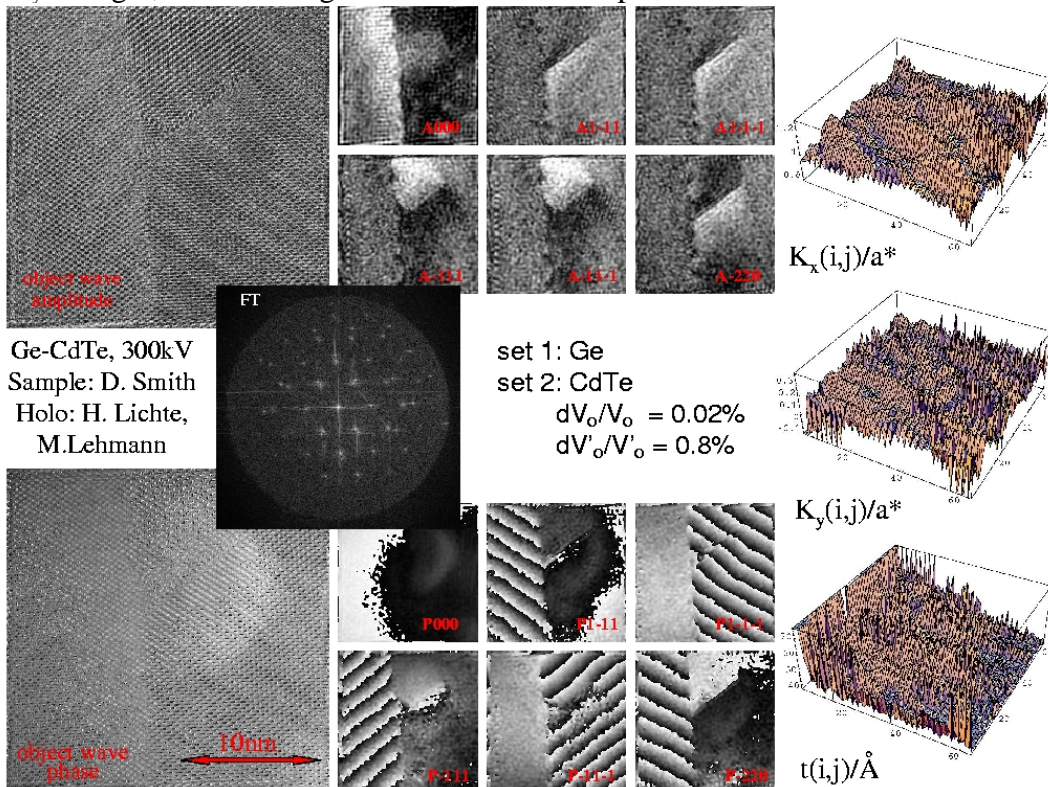


Fig.1: Retrieval of local thickness t and orientation \mathbf{K}_{xy} for an Ge-CdTe interface including different potential parameters

References:[1]. K. Scheerschmidt, Lecture Notes in Physics **486** (1997) 71 and Journal of Microsc. **190** (1998) 238-248. [2] K. Scheerschmidt, Microsc. Microanal. **9**, Suppl.6 (2003) 56 and WAVES 2003, Proc. 6th Int. Conf. Math. Num. Aspects Wave Prop., Eds.: G.C. Cohen and P. Joly, Springer Vlg., 2003, 607.